



### MCR 100 - 6/8 Plastic-Encapsulate Thyristors

Silicon Controlled Rectifier



#### FEATURES

Current- $I_{GT}$ : 200  $\mu$ A

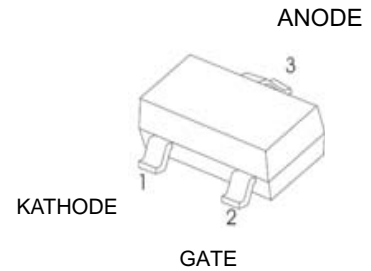
$I_{TRMS}$ : 0.8 A

$V_{RRM}/V_{DRM}$ : MCR100-6: 400 V

MCR100-8: 600 V

Operating and storage junction temperature range

$T_J, T_{stg}$ : -55°C to +150°C



**SOT-23**

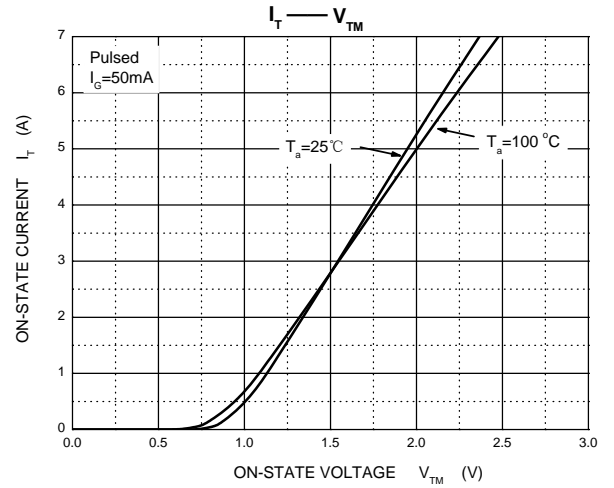
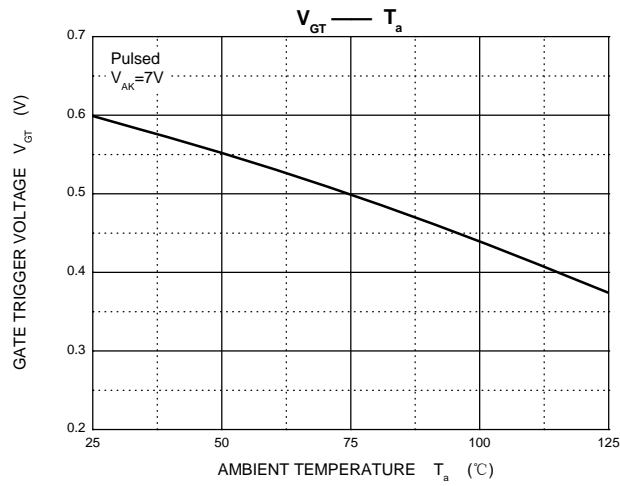
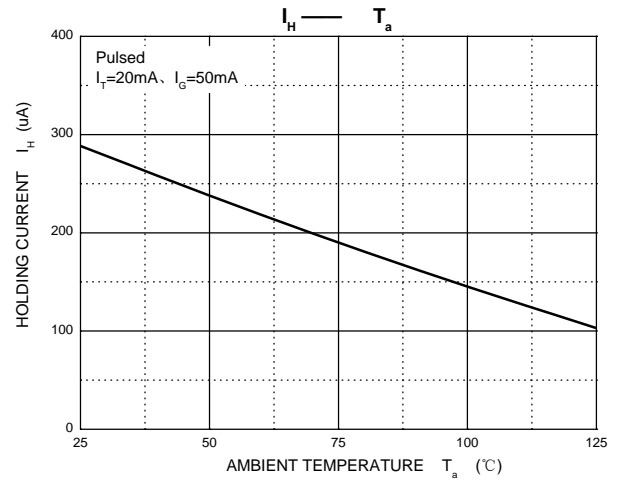
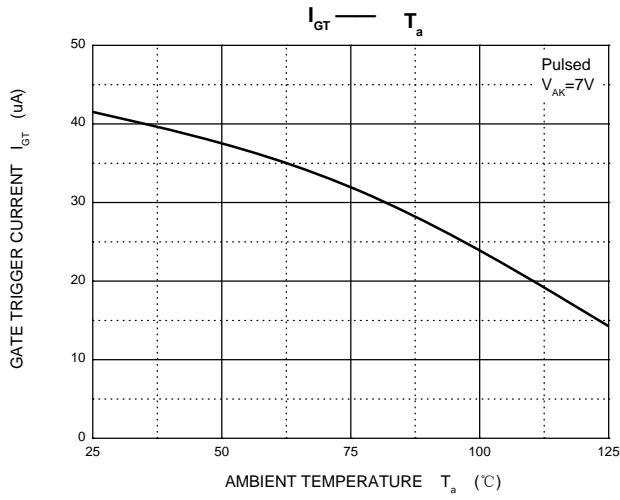
#### ELECTRICAL CHARACTERISTICS (Ta=25°C unless otherwise specified)

Parameter	Symbol	Test conditions	Min	Max	Unit	
On state voltage	$V_{TM}^*$	$I_{TM}=1A$		1.7	V	
Gate trigger voltage	$V_{GT}$	$V_{AK}=7V$		0.8	V	
Peak Repetitive forward and reverse blocking voltage  MCR100-6 MCR100-8	$V_{DRM}$ AND $V_{RRM}$	$I_{DRM}= 100\mu A$	400 600		V	
Peak forward or reverse blocking Current	$I_{DRM}$ $I_{RRM}$	$V_{AK}= \text{Rated}$ $V_{DRM}$ or $V_{RRM}$		10	$\mu$ A	
Holding current	$I_H$	$I_{HL}= 20mA, V_{AK} = 7V$		5	mA	
Gate trigger current	$I_{GT}$	$V_{AK}=7V$	A2	5	15	$\mu$ A
			A1	15	30	$\mu$ A
			A	30	80	$\mu$ A
			B	80	200	$\mu$ A

\* Forward current applied for 1 ms maximum duration, duty cycle  $\leq 1\%$ .



## Typical Characteristics

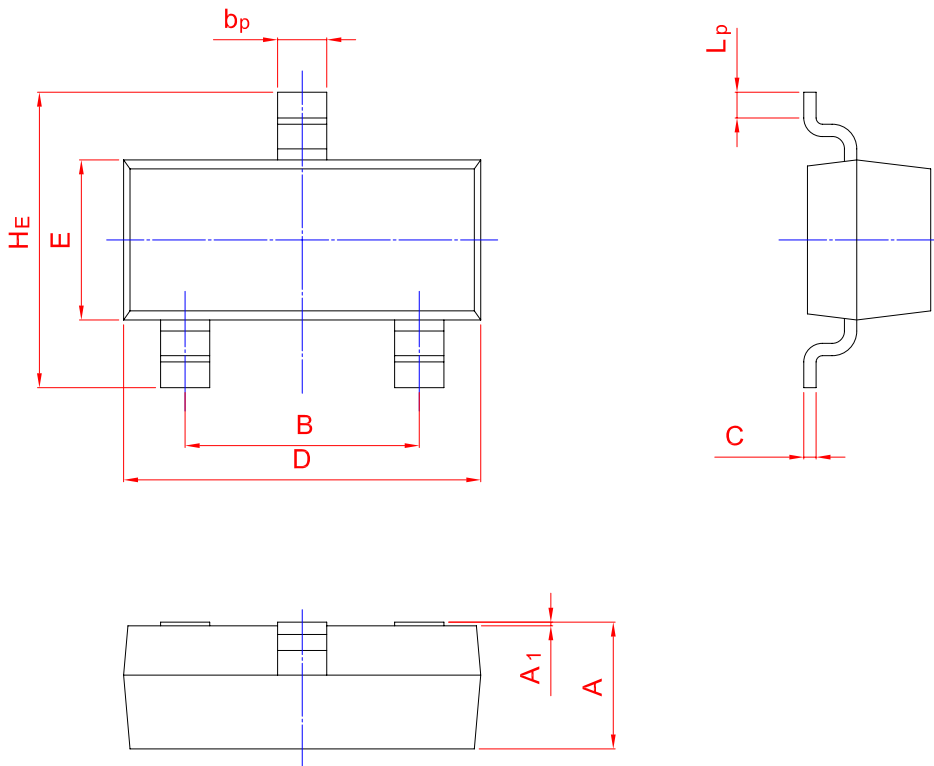
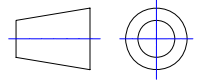




## PACKAGE OUTLINE

Plastic surface mounted package; 3 leads

SOT-23



UNIT	A	B	bp	C	D	E	HE	A1	Lp
mm	1.40	2.04	0.50	0.19	3.10	1.65	3.00	0.100	0.50
	0.95	1.78	0.35	0.08	2.70	1.20	2.20	0.013	0.20